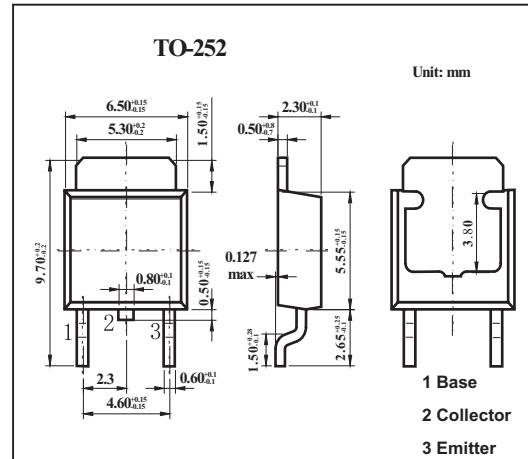


Silicon NPN Triple Diffusion Planar Type

2SD1250

■ Features

- High forward current transfer ratio h_{FE} which has satisfactory linearity
 - Low collector-emitter saturation voltage $V_{CE(sat)}$



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	200	V
Collector-emitter voltage	V _{C EO}	150	V
Emitter-base voltage	V _{EBO}	6	V
Collector current	I _C	2	A
Peak collector current	I _{CP}	3	
Collector power dissipation T _c = 25°C	P _C	1.3	W
		30	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V _{CBO}	I _C = 500 µA, I _E = 0	200			V
Collector-emitter voltage (Base open)	V _{CEO}	I _C = 5 mA, I _B = 0	150			V
Emitter-base voltage (Collector open)	V _{EBO}	I _E = 500 µA, I _C = 0	6			V
Collector-base cutoff current (Emitter open)	I _{CBO}	V _{CB} = 200 V, I _E = 0		50		µA
Emitter-base cutoff current (Collector open)	I _{EBO}	V _{EB} = 4 V, I _C = 0		50		µA
Forward current transfer ratio	h _{FE}	V _{CE} = 10 V, I _C = 150 mA	60		240	
		V _{CE} = 10 V, I _C = 400 mA	50			
Base-emitter voltage	V _{BE}	V _{CE} = 10 V, I _C = 400 mA		1.0		V
Collector-emitter saturation voltage	V _{CESat}	I _C = 500 mA, I _B = 50 mA		1.0		V
Transition frequency	f _T	V _{CE} = 10 V, I _C = 0.5 A, f = 1 MHz		20		MHz

■ hFE Classification

Rank	Q	P
hFE	60 to 140	100 to 240